

P-Channel Power MOSFET

-30V, -3A, 60mΩ

Features

- Advance Trench Process Technology
- High Density Cell Design for Ultra Low Onresistance
- Pb-free plating
- RoHS compliant
- Halogen-free package

Application

- Load Switch
- PA Switch

KEY PERFORMANCE PARAMETERS				
PARAMETER		VALUE	UNIT	
V_{DS}		-30	V	
D (*****)	V _{GS} = -10V	60		
$R_{DS(on)}(max)$	$V_{GS} = -4.5V$	90	mΩ	
Q_g		9.52	nC	

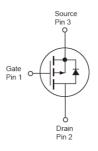












P-Channel MOSFET

Notes: Moisture sensitivity level: level 3. Per J-STD-020

ABSOLUTE MAXIMUM RATINGS (T _A = 25°C unless otherwise noted)					
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		V _{DS}	-30	V	
Gate-Source Voltage		V_{GS}	±20	V	
Continuous Drain Current (Note 1)	T _A = 25°C	I _D	-3	Α	
Pulsed Drain Current (Note 2)		I _{DM}	-10	Α	
Continuous Source Current (Diode Conduction)		I _S	-1.9	Α	
Total Dawar Dissination	T _A = 25°C	P _{DTOT}	1.25	W	
Total Power Dissipation	T _A = 70°C		0.8		
Operating Junction and Storage Temperature Range		T _J , T _{STG}	- 55 to +150	°C	

THERMAL PERFORMANCE					
PARAMETER	SYMBOL	LIMIT	UNIT		
Junction to Case Thermal Resistance	R _{eJC}	75	°C/W		
Junction to Ambient Thermal Resistance	R _{OJA}	100	°C/W		

Notes: $R_{\Theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistances. The case thermal reference is defined at the solder mounting surface of the drain pins. $R_{\Theta JA}$ is guaranteed by design while $R_{\Theta CA}$ is determined by the user's board design. $R_{\Theta JA}$ shown below for single device operation on FR-4 PCB in still air.



PARAMETER	CONDITIONS	SYMBOL	MIN	TYP	MAX	UNIT
Static (Note 3)		1	L	•		·
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = -250\mu A$	BV _{DSS}	-30			V
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	$V_{GS(TH)}$	-1.0	-1.5	-3.0	V
Gate Body Leakage	$V_{GS} = \pm 20V, V_{DS} = 0V$	I _{GSS}			±100	nA
Zero Gate Voltage Drain Current	V _{DS} = -24V, V _{GS} = 0V	I _{DSS}			-1	μA
On-State Drain Current	V _{DS} = -5V, V _{GS} = -10V	I _{D(ON)}	-6			Α
	$V_{GS} = -10V, I_D = -3A$	_		50	60	mΩ
Drain-Source On-State Resistance	V _{GS} = -4.5V, I _D = -2A	$R_{DS(ON)}$		75	90	
Forward Transconductance	$V_{DS} = -15V, I_{D} = -5A$	g _{fs}	4	7		S
Dynamic (Note 4)						
Total Gate Charge	$V_{DS} = -15V, I_D = -3A,$	Qg		9.52		
Gate-Source Charge		Q_{gs}		3.43		nC
Gate-Drain Charge	V _{GS} = -10V	Q_{gd}		1.71		
Input Capacitance		C _{iss}		551.57		
Output Capacitance	$V_{DS} = -15V, V_{GS} = 0V,$ f = 1.0MHz	C _{oss}		90.96		pF
Reverse Transfer Capacitance	1 = 1.0IVIM2	C _{rss}		60.79		
Switching (Note 5)					•	•
Turn-On Delay Time		t _{d(on)}		10.8		
Turn-On Rise Time	$V_{DD} = -15V,$ $R_{GEN} = 6\Omega,$	t _r		2.33		
Turn-Off Delay Time		t _{d(off)}		22.53		ns
Turn-Off Fall Time	$I_D = -1A$, $V_{GS} = -10V$,	t _f		3.87		
Source-Drain Diode (Note 3)		•		•	•	•
Forward On Voltage	I _S = -1.9 A, V _{GS} = 0V	V _{SD}		-0.8	-1.3	V

Notes:

- 1. Pulse width limited by the maximum junction temperature.
- 2. Surface Mounted on FR4 Board, $t \le 5$ sec.
- 3. Pulse test: PW \leq 300 μ s, duty cycle \leq 2%.
- 4. For DESIGN AID ONLY, not subject to production testing.
- 5. Switching time is essentially independent of operating temperature.





ORDERING INFORMATION

PART NO.	PACKAGE	PACKING
TSM3401CX RFG	SOT-23	3,000pcs / 7" Reel

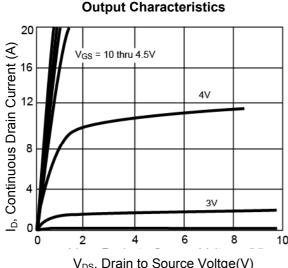
Note:

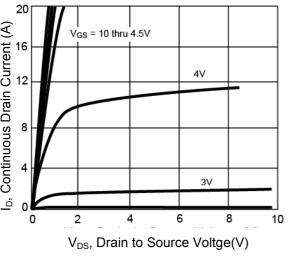
- 1. Compliant to RoHS Directive 2011/65/EU and in accordance to WEEE 2002/96/EC
- 2. Halogen-free according to IEC 61249-2-21 definition

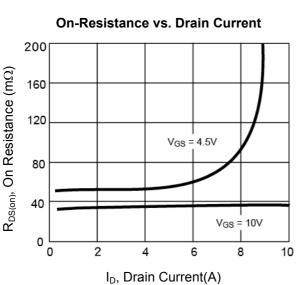


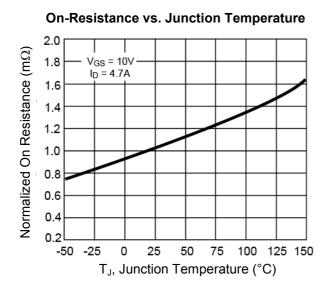
CHARACTERISTICS CURVES

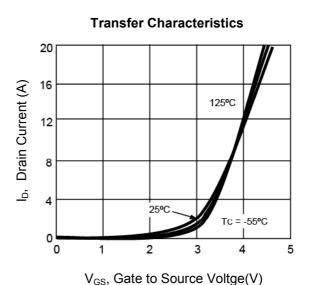
 $(T_A = 25^{\circ}C \text{ unless otherwise noted})$

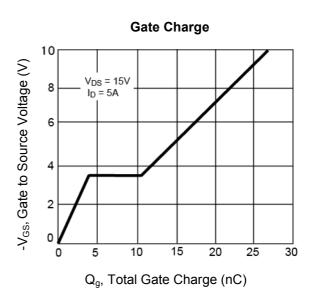


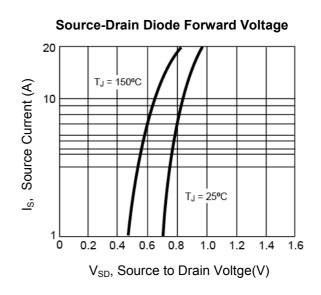








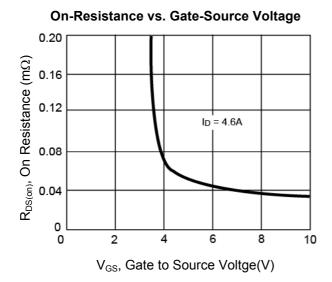


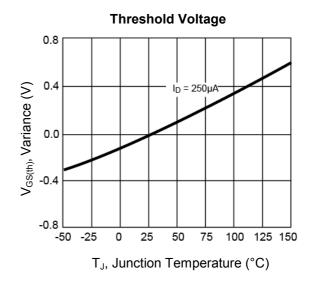


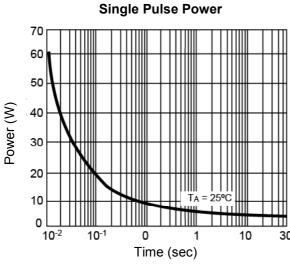


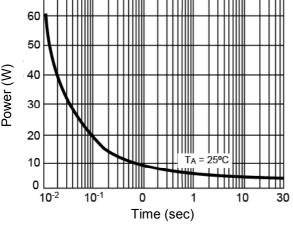
CHARACTERISTICS CURVES

 $(T_A = 25^{\circ}C \text{ unless otherwise noted})$

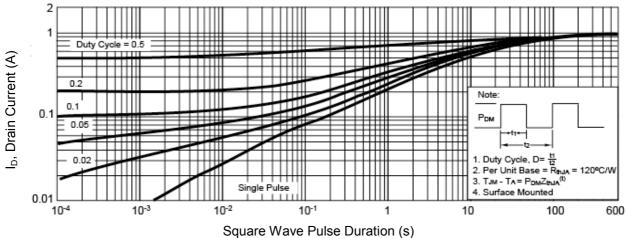






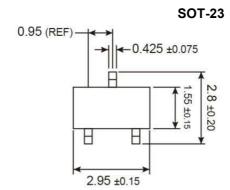


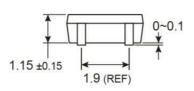
Normalized Thermal Transient Impedance Curve

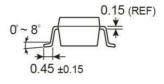




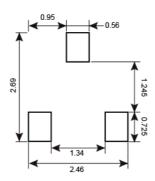
PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)







SUGGESTED PAD LAYOUT (Unit: Millimeters)



MARKING DIAGRAM



Y = Year Code

M = Month Code for Halogen Free Product

 $oldsymbol{O}$ =Jan $oldsymbol{P}$ =Feb $oldsymbol{Q}$ =Mar $oldsymbol{R}$ =Apr

S = May T = Jun U = Jul V = Aug

W =Sep X =Oct Y =Nov Z =Dec

L = Lot Code (1~9, A~Z)





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